

NTSV30100CT

Product Preview

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.471\text{ V}$ at $I_F = 5\text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

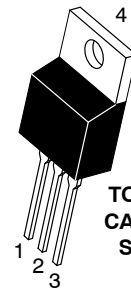
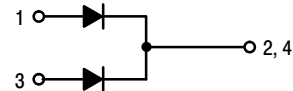
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



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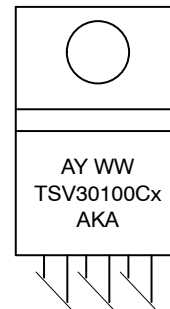
<http://onsemi.com>

PIN CONNECTIONS



TO-220AB
CASE 221A
STYLE 6

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
AKA = Polarity Designator
x = G or H
G = Pb-Free Package
H = Halide-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (Rated V_R , $T_C = 115^\circ\text{C}$)	$I_{F(AV)}$ Per device Per diode	30 15	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz, $T_C = 110^\circ\text{C}$)	I_{FRM} Per device Per diode	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	100	A
Operating Junction Temperature	T_J	-40 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 70	$^\circ\text{C}/\text{W}$ $^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 7.5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 7.5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_J = 125^\circ\text{C}$)	V_F	0.509 0.575 0.751 0.471 0.539 0.662	- - 1.05 - - 0.82	V
Maximum Instantaneous Reverse Current (Note 1) ($V_R = 70\text{ V}$, $T_J = 25^\circ\text{C}$) ($V_R = 70\text{ V}$, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	I_R	11.2 7.9 63 19.1	 500 35	μA mA μA mA

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

ORDERING INFORMATION

Device	Package	Shipping
NTSV30100CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSV30100CTH	TO-220AB (Halide-Free)	50 Units / Rail

TYPICAL CHARACTERISTICS

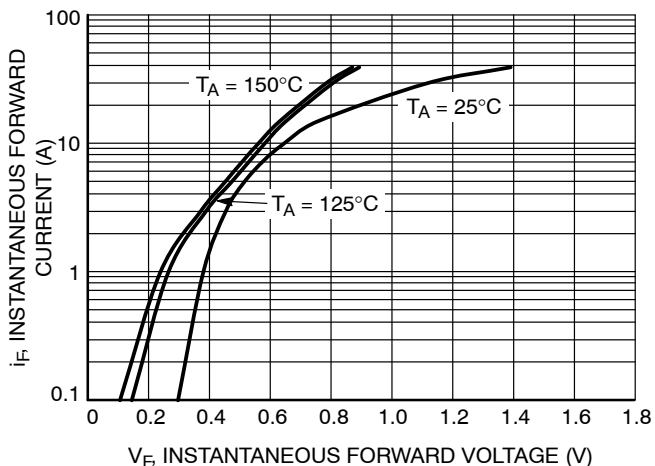


Figure 1. Typical Instantaneous Forward Characteristics

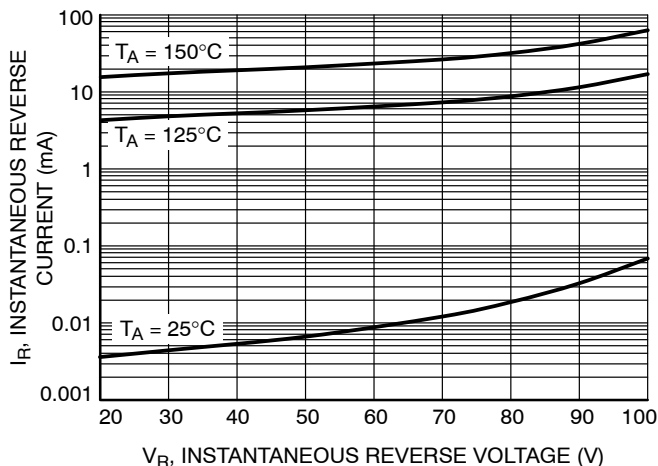


Figure 2. Typical Reverse Characteristics

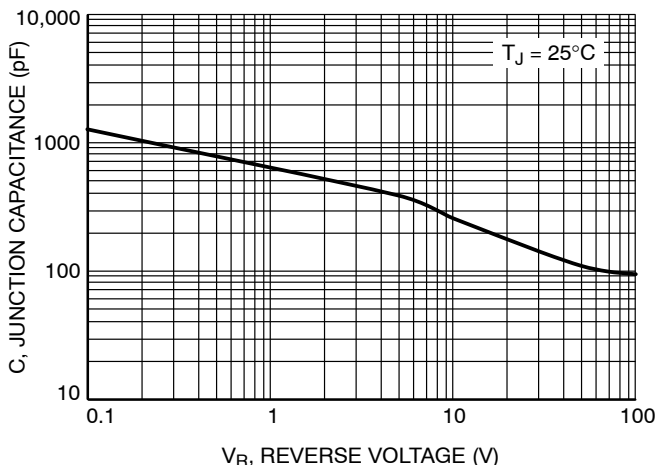


Figure 3. Typical Junction Capacitance

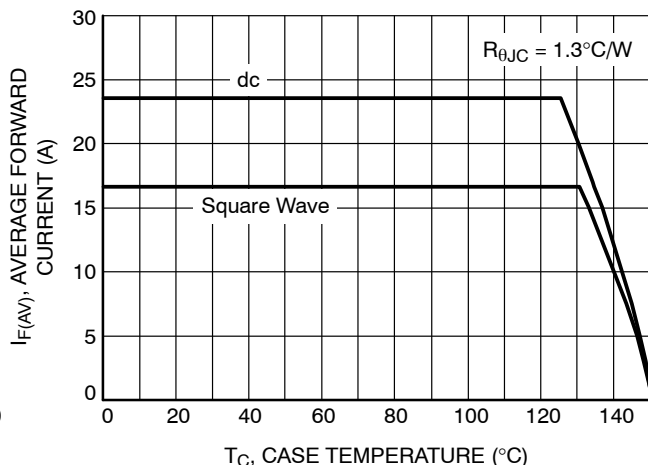


Figure 4. Current Derating per Leg

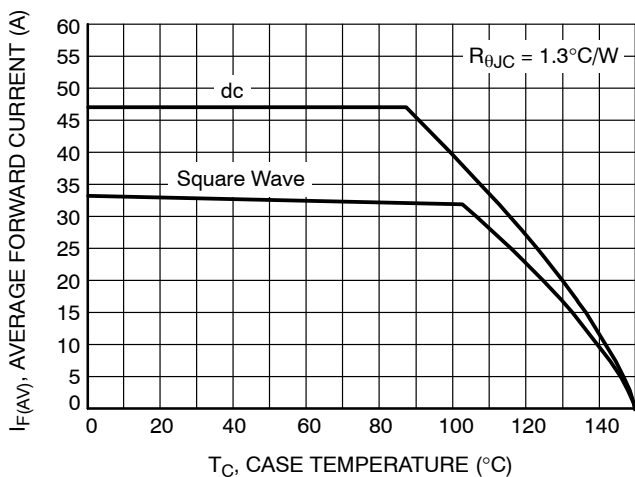


Figure 5. Current Derating

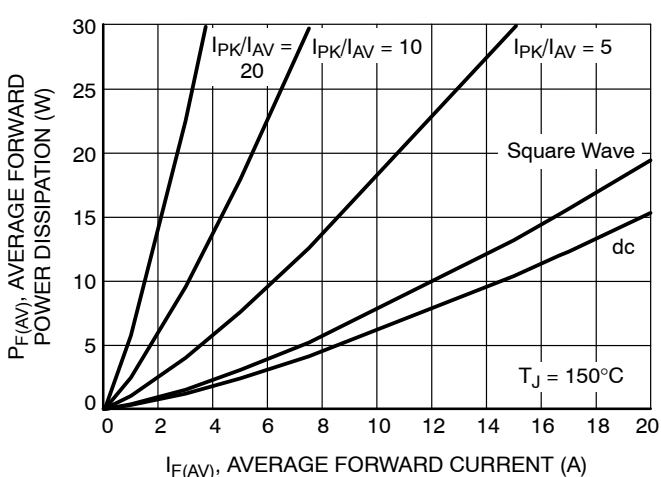


Figure 6. Forward Power Dissipation

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TYPICAL CHARACTERISTICS

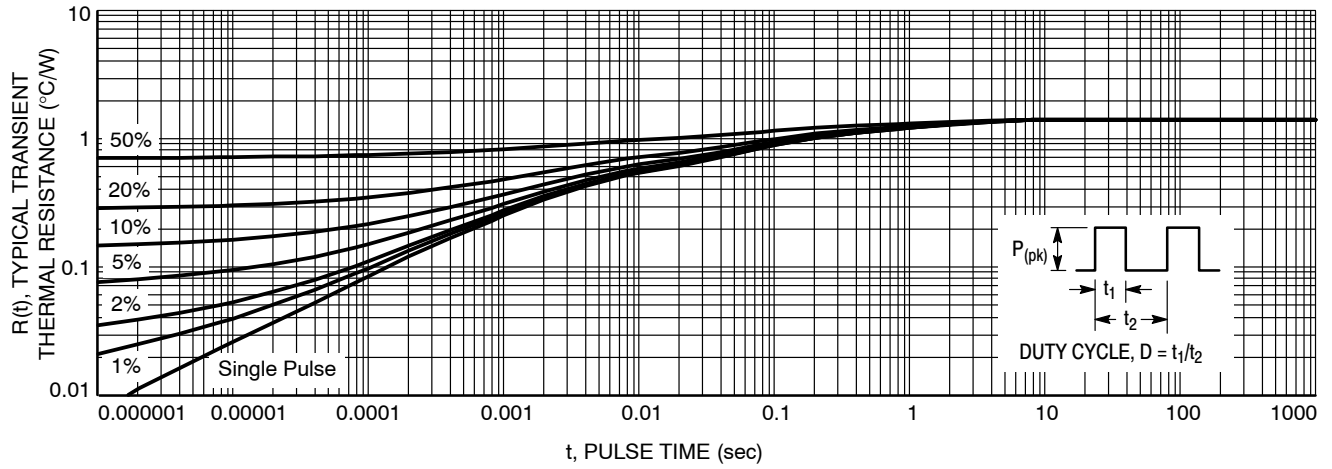
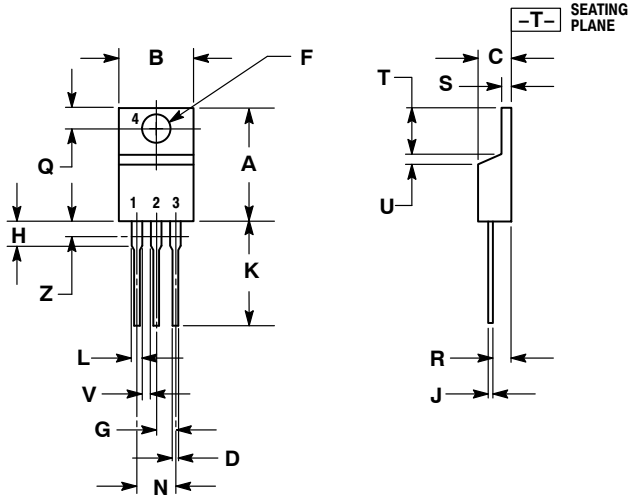


Figure 7. Typical Transient Thermal Response

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PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AG



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:

- PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

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